

ABSTRACT OF THE DISCLOSURE

A chemical oxide film formed on a semiconductor substrate is formed by wet cleaning using a strongly acidic solution so that the adhesion of impurities to the chemical oxide film can be reduced between a wet cleaning process and an insulation film forming process. This makes it possible to prevent insulation degradation of a gate insulation film when the gate insulation film embracing the chemical oxide film is formed in the insulation film forming process in which low-temperature processing is conducted.